



晶体管 TRANSISTOR A940A

主要参数 MAIN CHARACTERISTICS

I_c	-1.5A
V_{CE0}	-150V
P_c	25W

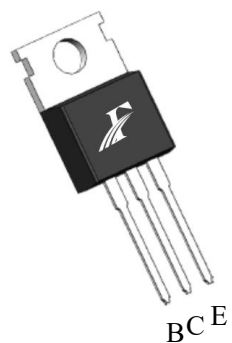
产品特性 FEATURES

硅外延	Epitaxial silicon
高开关速度	High switching speed
RoHS 产品	RoHS product
与 C2073 互补	Complementary to C2073

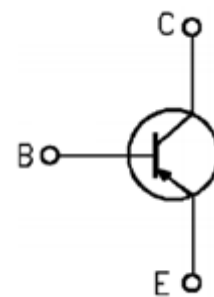
用途 APPLICATIONS

高频开关电源	High frequency switch power supply
一般功率放大电路	Commonly power amplifier circuit
高频功率变换	High frequency power transform

封装形式 Package



TO-220



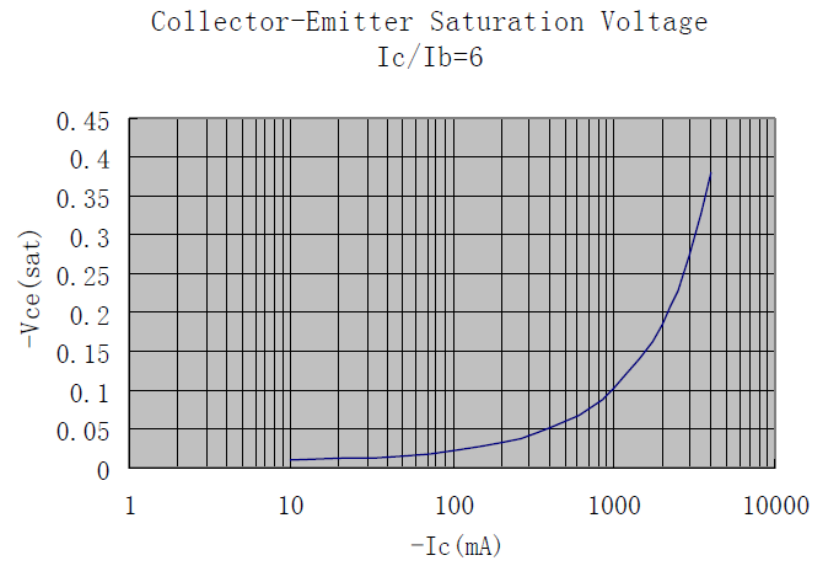
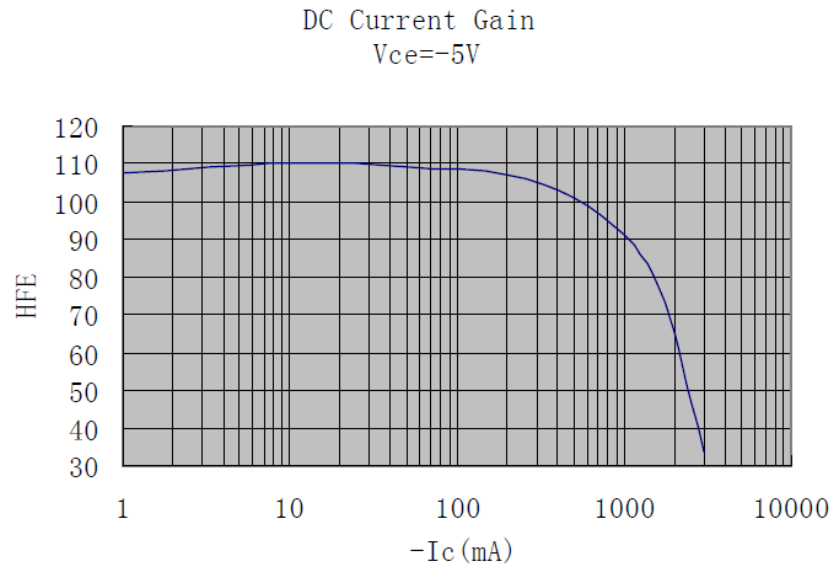
绝对最大额定值 ABSOLUTE RATINGS ($T_c=25^\circ\text{C}$)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
集电极—基极直流电压 Collector- Base Voltage ($I_E=0$)	V_{CBO}	-180	V
集电极—发射极直流电压 Collector- Emitter Voltage ($I_B=0$)	V_{CEO-}	-150	V
发射极—基极直流电压 Emitter-Base Voltage ($I_C=0$)	V_{EBO}	-6	V
最大集电极直流电流 Collector Current (DC)	I_c	-1.5	A
最大集电极耗散功率 Total Dissipation (TO-220)	P_c	25	W
最高结温 Junction Temperature	T_j	150	$^\circ\text{C}$
贮存温度 Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$

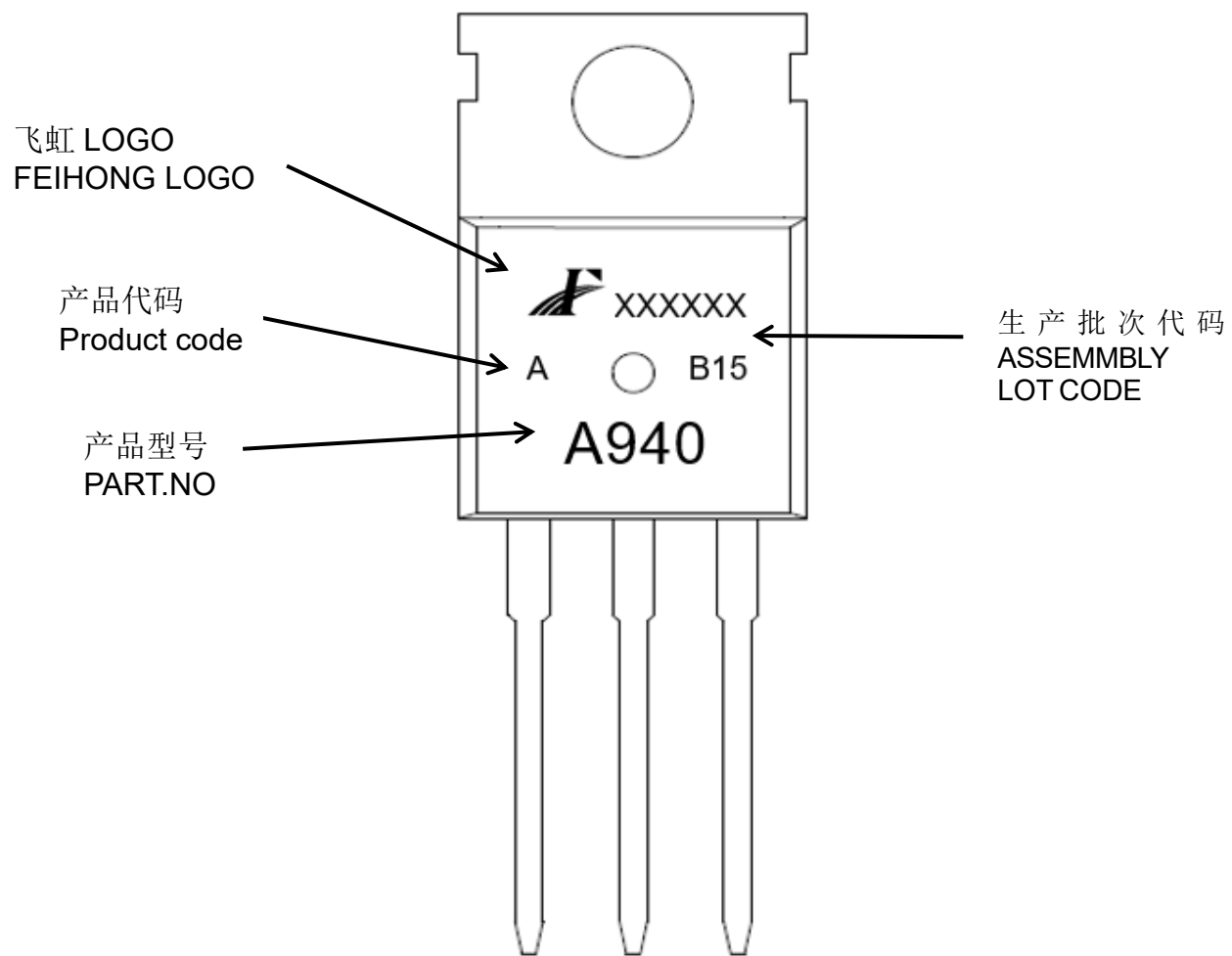
电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	测试条件 Tests conditions	最小值 (min)	典型值 (typ)	最大值 (max)	单位 Unit
$V(BR)_{CBO}$	$I_C = -100\mu A, I_E = 0$	-180	-	-	V
$V(BR)_{CEO}$	$I_C = -2mA, I_B = 0$	-150	-	-	V
$V(BR)_{EBO}$	$I_E = -100\mu A, I_C = 0$	-6	-	-	V
I_{CBO}	$V_{CB} = -180V, I_E = 0$	-	-	-10	μA
I_{EBO}	$V_{EB} = 7V, I_C = 0$	-	-	-10	μA
$h_{FE}(1)$	$V_{CE} = -5V, I_C = -0.5A$	80	-	240	-
$V_{CE(sat)}$	$I_C = -0.5A, I_B = -0.05A$	-	-	-1	V

典型特性曲线 Electrical Characteristics



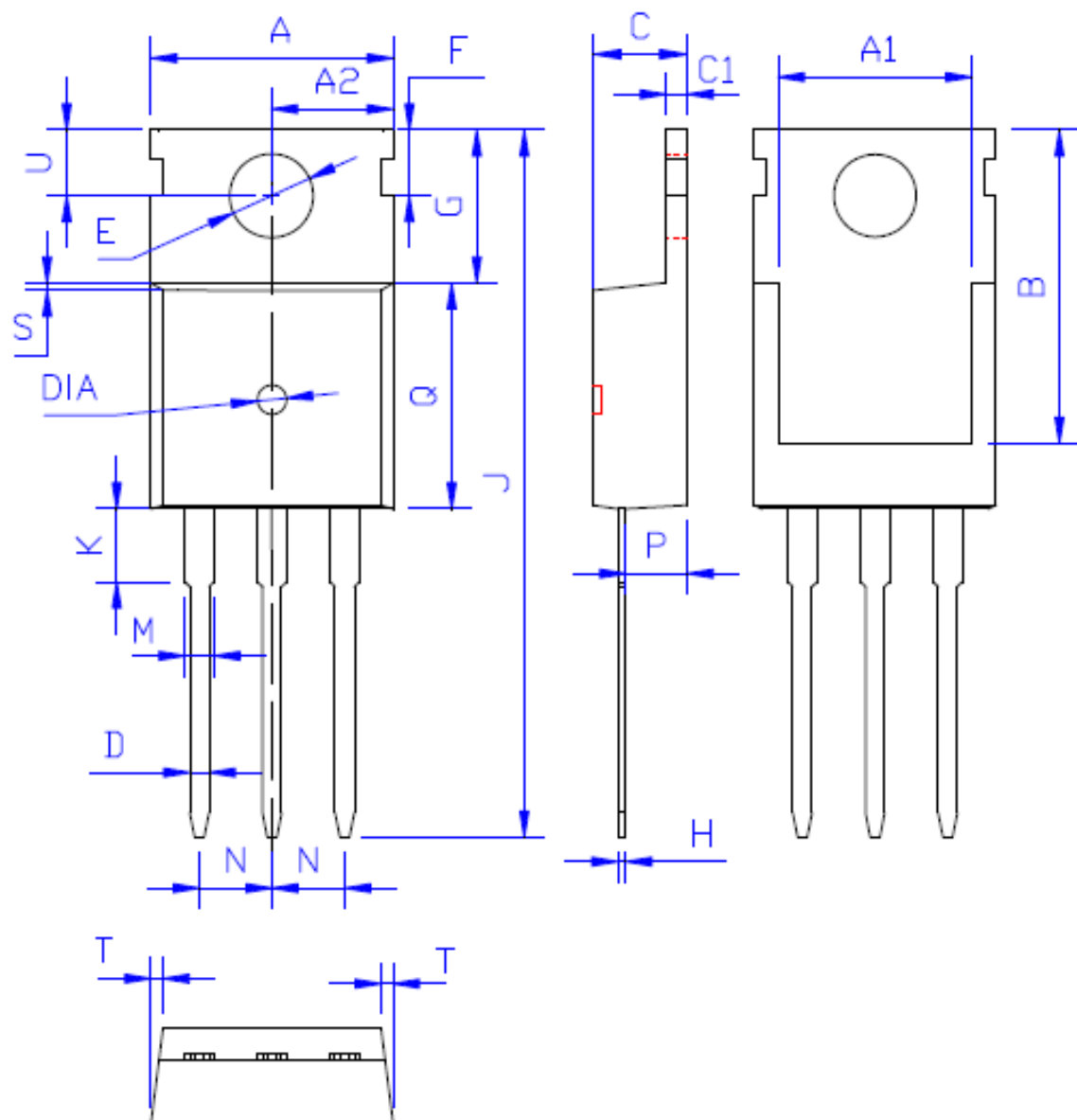
印记 Marking:



外形尺寸:

Package Dimension:

TO-220



DIM	MILLIMETERS
A	10.00±0.30
A1	8.00±0.30
A2	5.00±0.30
B	13.20±0.40
C	4.50±0.20
C1	1.30±0.20
D	0.80±0.20
E	3.60±0.20
F	3.00±0.30
G	6.60±0.40
H	0.50±0.20
J	28.88±0.50
K	3.00±0.30
M	1.30±0.30
N	Typical 2.54
P	2.40±0.40
Q	9.20±0.40
S	0.25±0.15
T	0.25±0.15
U	2.80±0.30
DIA	宽 1.50±0.10 深 0.50 MAX

(Unit: mm)